

MBRD6100CT

Technical Data Data Sheet N0811, Rev. A



MBRD6100CT SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- "-A" is an AEC-Q101 qualified device
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

Maximum Ratings:

Characteristics	Symbol	Condition Max.		Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	100	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle $@T_c = 105^{\circ}C$, rectangular wave form	3(Peg Leg) 6(Peg Device)	А
Peak One Cycle Non-Repetitive Surge Current(Peg Leg)	I _{FSM}	8.3 ms, half Sine pulse	80	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Peg Leg) *	V _{F1}	@ 3A, Pulse, T _J = 25 °C	0.78	0.85	V
	V _{F2}	@ 3A, Pulse, T _J = 125 °C	0.64	0.70	V
Reverse Current (Peg Leg) *	I _{R1}	$@V_R = rated V_{R,} T_J = 25 \circ C$	0.001	1.0	mA
	I _{R2}	$@V_R = rated V_{R,} T_J = 125 \circ C$	0.3	6.0	mA
Junction Capacitance(Peg Leg)	CT	$@V_{R} = 5V, T_{C} = 25 \text{ °C}, f_{SIG} = 1MHz$	160	300	pF

* Pulse width < 300 μ s, duty cycle < 2%

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Thermal-Mechanical Specifications:

Ratings and Characteristics Curves

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to + 150	°C
Typical Thermal Resistance Junction to Case(Peg Leg)	R _{0JC}	-	3.5	°C/W
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			



Fig.1-Typical Junction Capacitance



Fig.2-Typical Reverse Characteristics



Fig.3-Typical Instantaneous Forward Voltage Characteristics

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Technical Data

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RoHS

Mechanical Dimensions DPAK



	Millim	neters	Inches		
SYMBOL	Min.	Max.	Min.	Max.	
A	2.20	2.40	0.087	0.094	
A1	0.00	0.127	0.000	0.005	
b	0.66	0.86	0.026	0.034	
с	0.46	0.60	0.018	0.024	
D	6.50	6.70	0.256	0.264	
D1	5.13	5.46	0.202	0.215	
D2	4.83 REF.		0.190 REF.		
E	6.00	6.20	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.70	10.40	0.381	0.409	
L1	2.90 REF.		0.144 REF.		
L2	1.40	1.70	0.055	0.067	
L3	1.60 REF.		0.063 REF.		
L4	0.60	1.00	0.024	0.039	
Φ	1.10	1.30	0.043	0.051	
Θ	0°	8°	0°	8°	
h	0.00	0.30	0.000	0.012	
V	5.35 REF.		0.211 REF.		

MBR

D

6

100 СТ

SSG

YΥ

L

WW

Ordering Information

Device	Package	Shipping
MBRD6100CT	DPAK (Pb-Free)	2500pcs / reel
MBRD6100CTTR	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel Packaging specification.

Marking Diagram



Where XXXXX is YYWWL

- = Device Type
- = Package type
- = Forward Current (6A) = Reverse Voltage (100V)
- = Configuration
- = SSG

= Year

= Week

= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Carrier Tape Specification DPAK



SYMBOL	Millimeters		
STMBOL	Min.	Max.	
A	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Φ1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

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